





**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
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Note:

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Fig.1 Gate-Charge Characteristics

Fig.2 Capacitance Characteristics

Fig.3 Power Dissipation

Fig.4 Typical output Characteristics

Fig.5 Threshold Voltage V.S Junction T ( )-44(ha)11(nne171 0 595.304.49 Tm0.32 211.5)6(d Vol)7(t)-4(a)n-US



g On es stance S Gate Source o tage

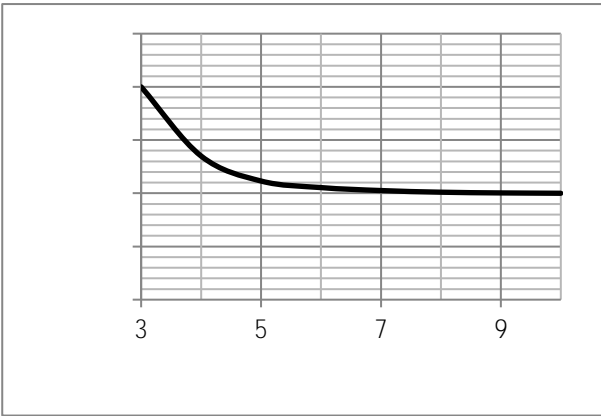


Fig.9 SOA Maximum Safe Operating Area

g On es stance S unct on emperature

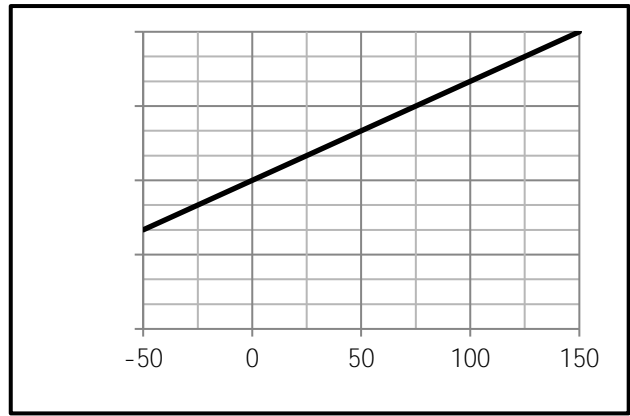


Fig.10 ID-Junction Temperature

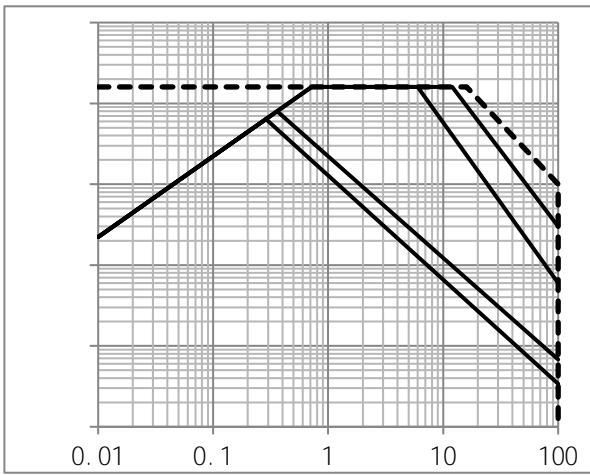


Fig.11 Switching Time Measurement Circuit

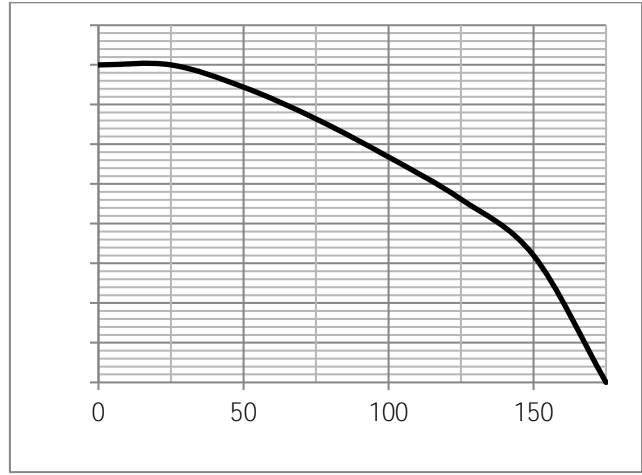


Fig.12 Gate Charge Waveform

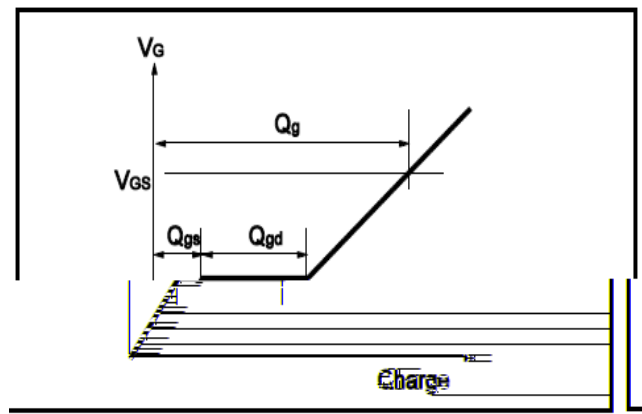
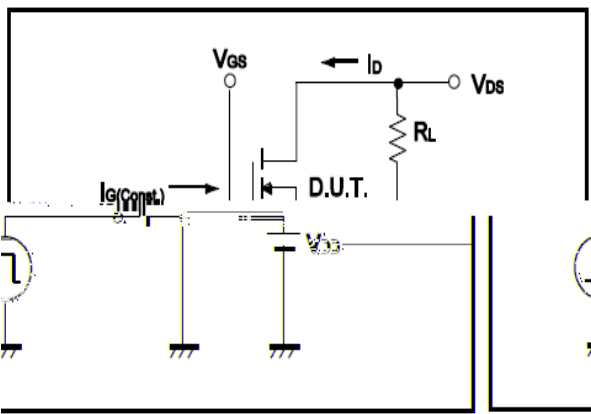




Fig.13 Switching Time Measurement Circuit

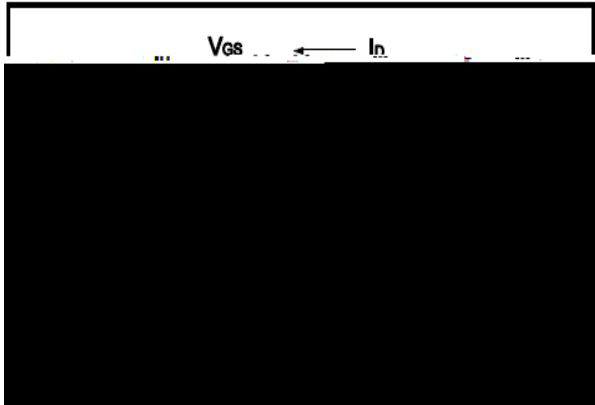


Fig.14 Gate Charge Waveform

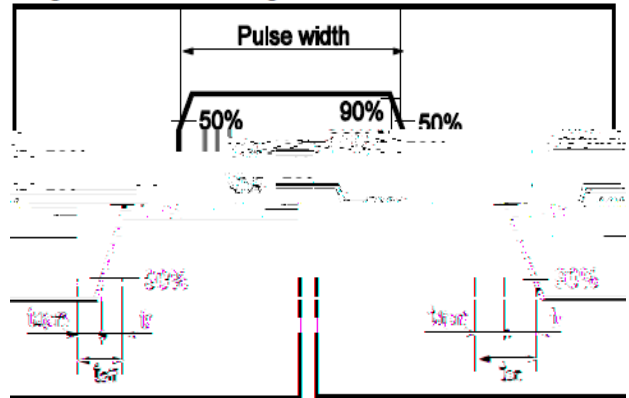


Fig.15 Avalanche Measurement Circuit

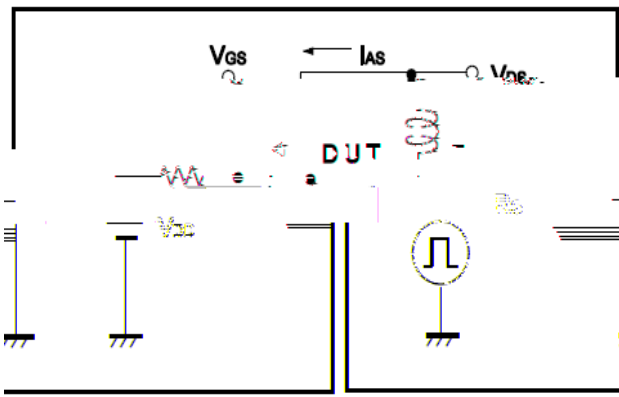
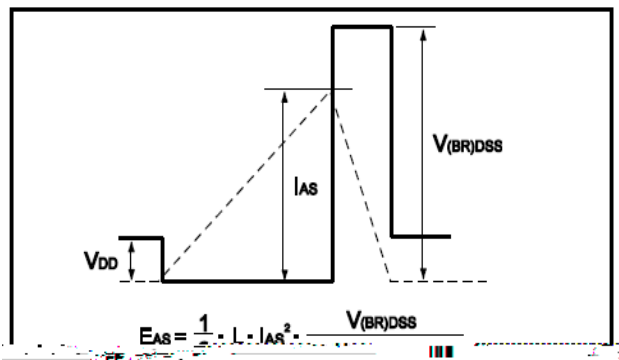


Fig.16 Avalanche Waveform





Dimensions TO-252

Unit mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

